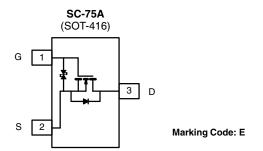




# N-Channel 60 V (D-S) MOSFET

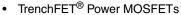
PRODUCT SUMMARY					
V <sub>DS(min.)</sub> (V)	$V_{DS(min.)}(V) \qquad R_{DS(on)}(\Omega)$		I <sub>D</sub> (mA)		
60	1.25 at V <sub>GS</sub> = 10 V	1 to 2.5	330		



Ordering Information: Si1022R-T1-GE3 (Lead (Pb)-free and Halogen-free)

#### **FEATURES**





• Low On-Resistance: 1.25  $\Omega$ 

Low Threshold: 2.5 V

Low Input Capacitance: 30 pFFast Switching Speed: 25 ns

• Low Input and Output Leakage

Miniature Package

ESD Protected: 2000 V

• Compliant to RoHS Directive 2002/95/EC

#### **APPLICATIONS**

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- · Battery Operated Systems
- Solid State Relays

#### **BENEFITS**

- · Low Offset Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Error Voltage
- Small Board Area

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	60	_ v	
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Ocation Desire Ocameral	T <sub>A</sub> = 25 °C	I_	330	mA	
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> = 85 °C	- I <sub>D</sub>	240		
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	650		
Danier Discipation	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	250	mW	
Power Dissipation <sup>a</sup>	T <sub>A</sub> = 85 °C	, p	130		
Thermal Resistance, Maximum Junction-to-Ambient <sup>a</sup>		R <sub>thJA</sub>	500	°C/W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

#### Notes:

a. Surface mounted on FR4 board, power applied for  $t \le 10$  s.

ROHS COMPLIANT HALOGEN FREE

# Vishay Siliconix



<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$	60			٧	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 0.25 \text{ mA}$	1		2.5	V	
Gate-Body Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			± 150		
	I <sub>GSS</sub>	T <sub>J</sub> = 85 °C			± 500		
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 20	nA	
		$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$			10		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	T <sub>J</sub> = 85 °C			100		
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
On Chata Duain Commanda	lac s	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}$	500			mA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 7.5 \text{ V}, V_{GS} = 10 \text{ V}$	800			IIIA	
		$V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$			3.0		
Drain-Source On-State Resistance <sup>a</sup>	Brack	T <sub>J</sub> = 125 °C			5.0	Ω	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$			1.25	52	
		T <sub>J</sub> = 125 °C			2.25		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_{D} = 200 \text{ mA}$	100			mS	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$V_{GS} = 0 \text{ V, } I_{S} = 200 \text{ mA}$			1.3	<b>V</b>	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			30			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		6		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			2.5			
Gate Charge	Qg	$V_{DS} = 10 \text{ V}, I_D = 250 \text{ mA}, V_{GS} = 4.5 \text{ V}$			0.6	nC	
Switching <sup>b, c</sup>							
Turn-On Time	t <sub>(on)</sub>	$V_{DD} = 30 \text{ V}, R_{L} = 150 \Omega,$			25	ns	
Turn-Off Time	t <sub>(off)</sub>	$I_D = 200 \text{ mA}, V_{GEN} = 10 \text{ V}, R_g = 10 \Omega$			35	110	

#### Notes:

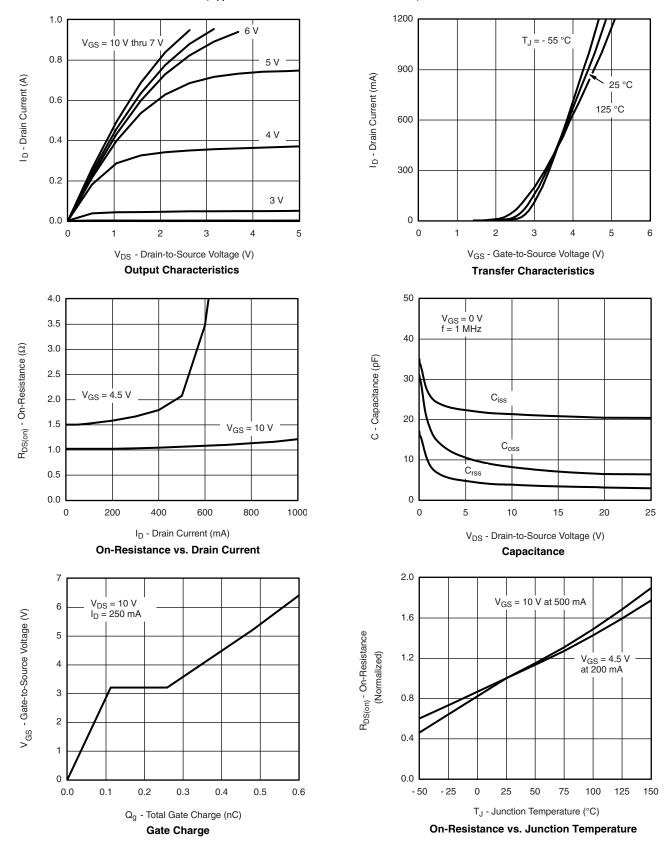
- a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





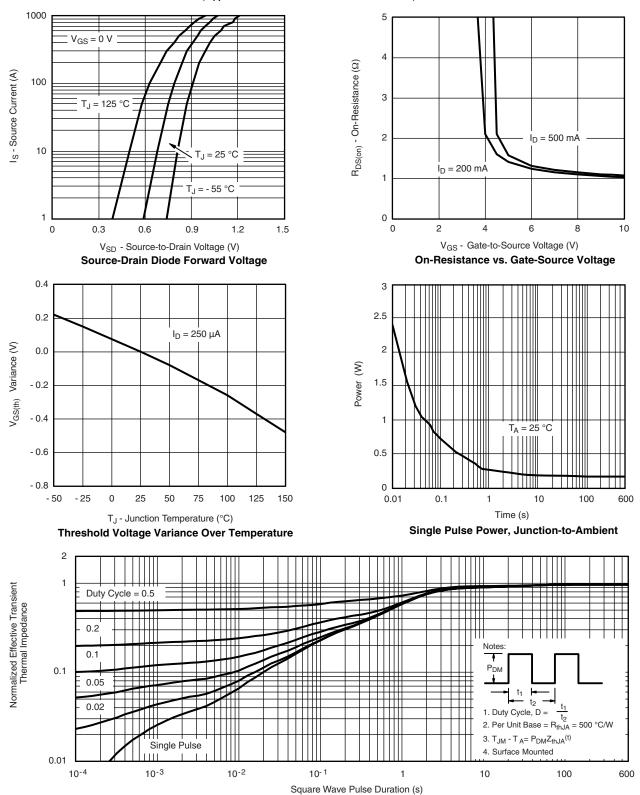
## **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



## Vishay Siliconix



#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

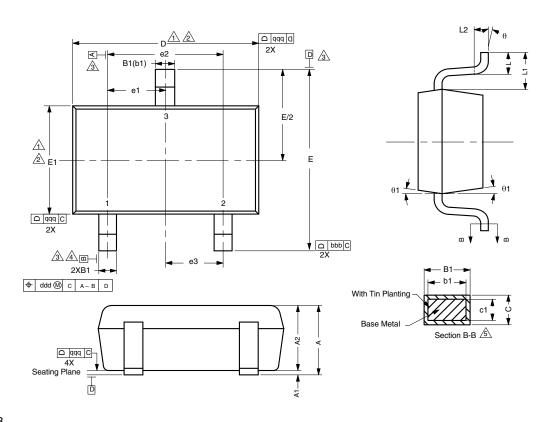


#### Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?71331">www.vishay.com/ppg?71331</a>.



### SC-75A: 3 Leads



DWG: 5868

#### Notes

Dimensions in millimeters will govern.

2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interelead flash, but including any mismatch between the top and bottom of the plastic body.

2 Datums A, B and D to be determined 0.10 mm from the lead tip.

4 Terminal positions are shown for reference only.

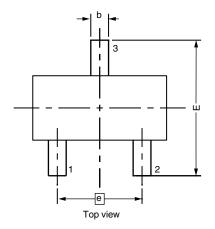
These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

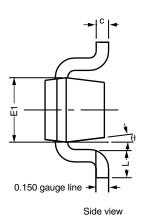
DIMENSIONS	TOLERANCES		
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.10		

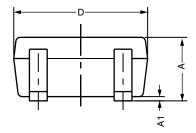
DIM.	N			
DIIVI.	MIN.	NOM.	MAX.	NOTE
Α	-	-	0.80	
A <sub>1</sub>	0.00	-	0.10	
A <sub>2</sub>	0.65	0.70	0.80	
B <sub>1</sub>	0.19	-	0.24	5
b <sub>1</sub>	0.17	-	0.21	
С	0.13	-	0.15	5
C <sub>1</sub>	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E <sub>1</sub>	0.66	0.76	0.86	1, 2
e <sub>1</sub>		0.50 BSC		
e <sub>2</sub>	1.00 BSC			
e <sub>3</sub>	0.50 BSC			
L	0.15	0.205	0.30	
L <sub>1</sub>	0.40 ref.			
L <sub>2</sub>	0.15 BSC			
θ	0°	-	8°	
$\theta_1$	4°	-	10°	

Vishay Siliconix

#### For Samsung only







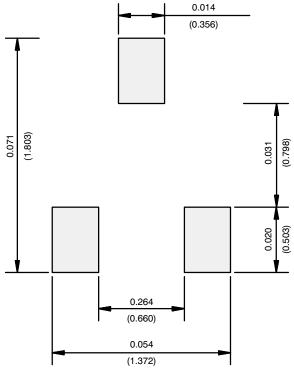
#### Notes

- (1) Millimeters will govern.
- (2) Dimension exclusive of mold gate burrs.
- (3) Dimension exclusive of mold flash and cutting burrs.

DIM.	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.60	0.70	0.80	0.024	0.028	0.031	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
b	0.18	0.22	0.32	0.007	0.009	0.013	
С	0.11	0.13	0.21	0.004	0.005	0.008	
D	1.48	1.58	1.68	0.058	0.062	0.066	
E	1.50	1.60	1.70	0.059	0.063	0.067	
E1	0.66	0.76	0.86	0.026	0.030	0.034	
е	0.95	1.00	1.05	0.037	0.039	0.041	
L	0.22	0.32	0.42	0.009	0.013	0.017	
θ	4°	7°	10°	4°	7°	10°	



#### **RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE

Document Number: 72603 Revision: 21-Jan-08



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Revision: 02-Oct-12 Document Number: 91000

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